

Dopant-Induced Local Pairing Inhomogeneity in $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$

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A new theoretical model is presented to study the nanoscale electronic inhomogeneity in high- T_c cuprates. In this model, we argue that the randomly distributed out-of-plane interstitial oxygen dopants induces locally the off-diagonal (i.e., hopping integral) disorder. This disorder modulates the superexchange interaction resulting from a large- U Hubbard model, which in turn changes the local pairing interaction. The microscopic self-consistent calculations shows that the large gap regions are registered to the locations of dopants. Large gap regions exhibit small and broader coherence peaks. These results are qualitatively consistent with recent STM observations on optimally doped $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$.

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One of the most striking features of high- T_c cuprate, $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$ (BSCCO), is the nanoscale electronic inhomogeneity as observed, for example, by the scanning tunneling microscopy (STM) [1, 2, 3, 4, 5, 6]. Earlier STM experiments shows that the spectra gap varies dramatically on a very short length scale, typically in the scale of $50\text{\AA}$. At the same time the low energy part of the tunneling spectra are extremely homogeneous spatially, except in the immediate vicinity of known defects in the CuO_2 plane [7, 8, 9]. Coherence peaks in regions with large gap are broadened and their height is reduced or peaks are entirely absent. Several scenarios have been proposed to understanding this surprising electronic inhomogeneity. It is commonly accepted that the hole doping in the CuO_2 planes is proportional to the concentration of out-of-plane oxygen dopant atoms. Thus the out-of-plane doping also introduces disorder. Therefore, it is tempting to speculate that poorly screened electrostatic potentials of the dopant atoms cause a variation in the local doping concentration, giving rise to the gap modulations [10, 11, 12]. Alternatively, one would ascribe the distinct electronic structures to the competition between two different electronic orders that exist intrinsically in the system— In the small gap regions, with high intensity sharp coherence peaks, the superconductivity wins; in the large gap regions, a pseudo-gap phase dominates with a competing order such as spin [13, 14, 15] or orbital [16] antiferromagnetism, or charge density wave [17]. The competing order scenario is supported by the STM data on the underdoped samples [18, 19] or on the optimally doped ones in the mixed state [20], where a checkerboard pattern in the local density of states (LDOS) has been observed. One distinctive feature of all these scenarios is that a uniform pairing interaction throughout the system has always been assumed.

Recent STM data on the optimally doped BSCCO [6] showed that the locations of oxygen dopants are positively correlated with the large gap regions with small charge density variations. It was proposed by Nunner *et al.* [21] that the dopant atoms modulate the local pairing

interaction, i.e., the local attractive coupling g between electrons are spatially dependent. In the phenomenological model of [21], the modulation of g is suggested to arise from a modification of local electronic structure parameters, but no concrete microscopic model was explored.

In this Letter we propose a microscopic model for the pair potential disorder. We argue that it originates from the modulation of the local pairing interaction induced by the doped oxygen atoms. The specific mechanism is based on an extended t - J model with the local superexchange interaction being modulated by the off-diagonal disorder (i.e., the electronic hopping integral). This specific mechanism on how the gap inhomogeneity might be triggered by the disorder in pair potential, is also consistent with the findings [22, 23] that τ_1 -type impurities rather than τ_3 -type impurities in the Nambu space are more relevant in the interpretation of the $\mathbf{q}$ structure observed in most Fourier-transformed STM experiments [24, 25, 26].

We find that the off-diagonal disorder, triggered by dopant atoms, produces a modulations of the gap across the sample. To be consistent with the experiment, we will assume that dopant atoms are interstitial. Each dopant atom therefore leads to a local modulation of the hopping matrix element on the neighboring links in Cu-O plane. This increased hopping will elevate the local superexchange interaction, which in turn leads to the local increase of the pair potential. Typical length scale of the modulation in response to the electronic distortion is set by the superconducting coherence length $\xi \sim 5a$ and is short in our model. We also find that the gap exhibited in the LDOS spectra reflects directly the local pair potential; and that the LDOS spectra in the regions of the large gap have coherence peaks that are moving out and are less sharp than the coherence peaks at small-gap regions. We believe the effect found here is a generic property of any model, where the pairing scale is set by the local superexchange.

As early as in 1987, Anderson suggested the relevance of the large- U limit of the Hubbard model to the prob-

lem of high- T_c superconductivity in cuprates [27] and the strong correlations are a central part of the high- T_c problem. To attack the present problem, we therefore start with a large- U Hubbard model with an off-diagonal disorder, defined on a two-dimensional square lattice:

$$\mathcal{H} = - \sum_{\langle \mathbf{ij} \rangle, \sigma} t_{\mathbf{ij}} c_{\mathbf{i}\sigma}^\dagger c_{\mathbf{j}\sigma} + \sum_{\mathbf{i}} (\epsilon_{\mathbf{i}} - \mu) c_{\mathbf{i}\sigma}^\dagger c_{\mathbf{i}\sigma} + U \sum_{\mathbf{i}} n_{\mathbf{i}\uparrow} n_{\mathbf{i}\downarrow}. \quad (1)$$

Here the quantities $c_{\mathbf{i}\sigma}^{(\dagger)}$ annihilates (creates) an electron on the $\mathbf{i}$ th site with spin σ , $t_{\mathbf{ij}}$ is the hopping integral between sites $\mathbf{i}$ and $\mathbf{j}$, $\epsilon_{\mathbf{i}}$ is the on-site energy, μ is the chemical potential, $n_{\mathbf{i}\sigma}$ is the spin-polarized number operator, and $\sum_{\langle \mathbf{ij} \rangle}$ indicates the summation over neighboring sites. Following the similar treatment to a large- U Hubbard model for a clean system [28, 29, 30], one can show that, in the large- U limit, the disordered Hubbard model is equivalent to the following model Hamiltonian:

$$\mathcal{H} = - \sum_{\langle \mathbf{ij} \rangle, \sigma} t_{\mathbf{ij}} c_{\mathbf{i}\sigma}^\dagger c_{\mathbf{j}\sigma} + \sum_{\mathbf{i}} (\epsilon_{\mathbf{i}} - \mu) c_{\mathbf{i}\sigma}^\dagger c_{\mathbf{i}\sigma} + \frac{1}{2} \sum_{\langle \mathbf{ij} \rangle} J_{\mathbf{ij}} [\mathbf{S}_{\mathbf{i}} \cdot \mathbf{S}_{\mathbf{j}} - \frac{1}{4} n_{\mathbf{i}} n_{\mathbf{j}}], \quad (2)$$

acting on the subspace of empty and singly-occupied sites only, where $\mathbf{S}_{\mathbf{i}}$ is the Heisenberg spin- $\frac{1}{2}$ operator, the local superexchange interaction $J_{\mathbf{ij}} = 4t_{\mathbf{ij}}^2/U$. In traditional disordered Hubbard model, the disorder is modeled through a random distribution of on-site (diagonal) energy while the hopping integrals are taken to be uniform. This approach cannot generate a direct modulation of the local pairing interaction, and the resultant pair potential can only be modulated near the known impurities through a local shift in effective chemical potential within a self-consistent solution.

Here we argue instead that the oxygen dopants modulate the local electronic hopping integral, and as a direct consequence, modulate the local pairing interaction through superexchange $J_{\mathbf{ij}}$. For the purpose of this discussion, we consider only the optimally doped regime. In this regime (and hopefully also in the overdoped regime), we believe that the slave-boson mean field approach might be a reasonable approximation [31]. In this approach, one first writes the electron operator as $c_{\mathbf{i}\sigma} = b_{\mathbf{i}}^\dagger f_{\mathbf{i}\sigma}$, with $f_{\mathbf{i}\sigma}$ and $b_{\mathbf{i}}$ being the operators for a spinon (a neutral spin- $\frac{1}{2}$ fermion) and a holon (a spinless charged boson). Due to the holon Bose condensation at low temperatures, the holon operator $b_{\mathbf{i}}$ is treated as a c -number and the quasiparticles are determined by the spinon degree of freedom only. Within the mean-field approximation, the Bogoliubov-de Gennes (BdG) equations can be derived as [32]:

$$\sum_{\mathbf{j}} \begin{pmatrix} H_{\mathbf{ij}} & \Delta_{\mathbf{ij}} \\ \Delta_{\mathbf{ij}}^\dagger & -H_{\mathbf{ij}} \end{pmatrix} \begin{pmatrix} u_{\mathbf{j}}^n \\ v_{\mathbf{j}}^n \end{pmatrix} = E_n \begin{pmatrix} u_{\mathbf{i}}^n \\ v_{\mathbf{i}}^n \end{pmatrix}, \quad (3)$$

with $H_{\mathbf{ij}} = -[t_{\mathbf{ij}} b_{\mathbf{i}} b_{\mathbf{j}}^* + \frac{J_{\mathbf{ij}}}{2} \chi_{\mathbf{ij}}] + (\epsilon_{\mathbf{i}} - \mu) \delta_{\mathbf{ij}}$. Here $u_{\mathbf{i}}^n$ and $v_{\mathbf{i}}^n$ are the Bogoliubov amplitudes corresponding to the eigenvalue E_n . The resonant-valence-bond (RVB) pairing order parameters (OP) $\Delta_{\mathbf{ij}}$, the bond OP $\chi_{\mathbf{ij}}$, and the spatially dependent hole density $\delta_{\mathbf{i}}$ are determined self-consistently: $\Delta_{\mathbf{ij}} = \frac{J_{\mathbf{ij}}}{2} \sum_n [u_{\mathbf{i}}^n v_{\mathbf{j}}^{n*} + u_{\mathbf{j}}^n v_{\mathbf{i}}^{n*}] \tanh\left(\frac{E_n}{2k_B T}\right)$, $\chi_{\mathbf{ij}} = \sum_n \{u_{\mathbf{i}}^{n*} u_{\mathbf{j}}^n f(E_n) + v_{\mathbf{i}}^n v_{\mathbf{j}}^{n*} [1 - f(E_n)]\}$ and $\delta_{\mathbf{i}} = 1 - 2 \sum_{\mathbf{i}, n} \{|u_{\mathbf{i}}^n|^2 f(E_n) + |v_{\mathbf{i}}^n|^2 [1 - f(E_n)]\}$ where k_B is the Boltzmann constant; $f(E) = [\exp(E/k_B T) + 1]^{-1}$ is the Fermi distribution function. The holon c -number is determined through $b_{\mathbf{i}} = \sqrt{\delta_{\mathbf{i}}}$. Here without the loss of generality, we have assumed $b_{\mathbf{i}}$ to be real. With exact diagonalization, we solve the BdG equations fully self-consistently. Once a converged solution is reached, the LDOS at zero temperature is then evaluated according to: $\rho_{\mathbf{i}}(E) = 2 \sum_n [|u_{\mathbf{i}}^n|^2 \delta(E_n - E) + |v_{\mathbf{i}}^n|^2 \delta(E_n + E)]$ where a factor 2 arises from the spin sum. The LDOS $\rho_{\mathbf{i}}(E)$ is proportional to the local differential tunneling conductance which can be measured in an STM experiment [33].

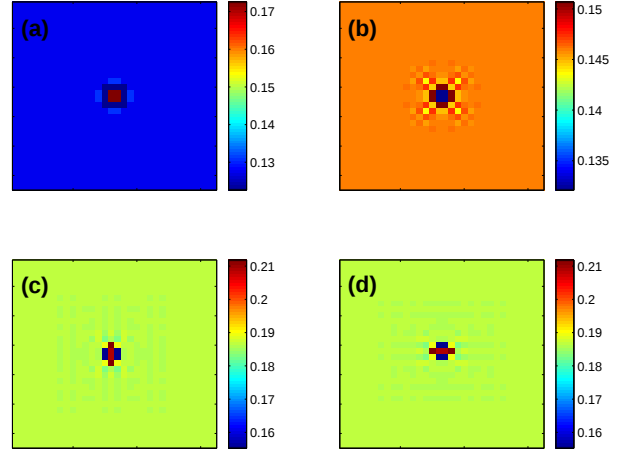


FIG. 1: (a) d -wave OP; (b) hole density distribution; (c)-(d) x - and y -oriented RVB bond OP. They are obtained from a solution to an untied single dopant.

In the numerical calculation, we construct a superlattice with the square lattice $N_x \times N_y$ as a unit supercell. As detailed in Ref. [34], this method can provide the required energy resolution. Throughout the work, we take the size of the unit supercell $N_a = 32 \times 32$, the number of supercells $N_c = 6 \times 6$, the temperature $T = 0$, the Hubbard interaction $U = 10$. As we have already mentioned before, the hopping integral $\tilde{t}_{ij}$ should be modified by the presence of out-of-plane oxygen dopants. Without a detailed first-principle calculation, the extent of this modification is unknown. Therefore, we parameterize the hopping integral in the form [35]: $t_{\mathbf{ij}} = t_{\mathbf{ij}}^0 + \delta t_{\mathbf{ij}}$, where $t_{\mathbf{ij}}^0$ is the bare hopping integral. We choose $t_{\mathbf{ij}}^0$ to be $t = 1$ for the nearest-neighboring hopping and $t' = -0.3$ for the next nearest-neighboring hopping. For the resultant superexchange interactions,

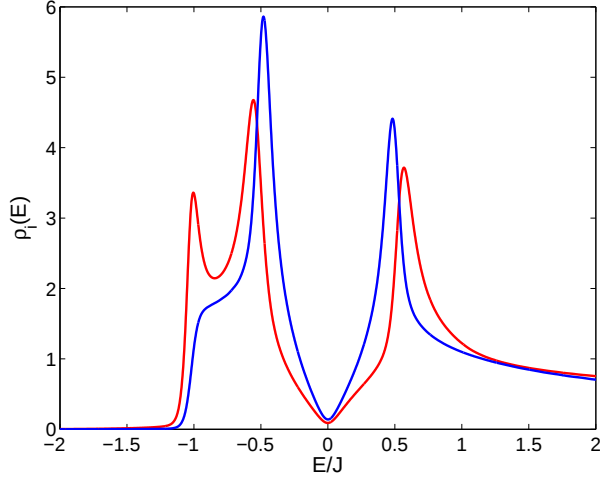


FIG. 2: LDOS spectrum at the “on-dopant” site with a gap $\Delta_1 \sim 0.6$ (red line) and in a location far away from the dopant with a gap $\Delta_0 \sim 0.5$ (blue line).

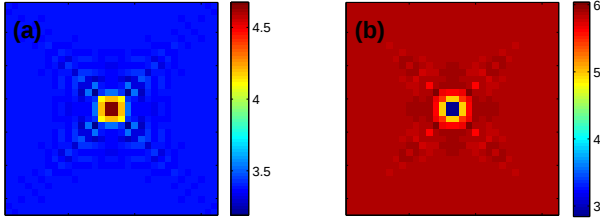


FIG. 3: LDOS maps $\rho_l(E)$ in real space for energy at $E = \Delta_1$ (a) and $E = \Delta_0$ (b).

only those for the nearest-neighbor pairs are considered, with a new energy scale $J = 4t^2/U = 0.4$. By assuming that dopant atoms are interstitial, as suggested by the STM observations [19, 23], we restrict for simplicity the change in the hopping integral to the four bonds forming a plaquette in the Cu-O plane, at the location sharply below each oxygen dopant and take $\delta t_{ij} = 0.2$. No site-diagonal disorder are introduced, i.e., $\epsilon_i = 0$. The chemical potential is tuned such that the averaged hole density from the self-consistency solution is about 0.14. The obtained spatial variation of the d -wave is defined as $\Delta_d(\mathbf{i}) = \frac{1}{4}[\Delta_{\hat{x}}(\mathbf{i}) + \Delta_{-\hat{x}}(\mathbf{i}) - \Delta_{\hat{y}}(\mathbf{i}) - \Delta_{-\hat{y}}(\mathbf{i})]$. Throughout the following discussion, the energy is measured in units of J .

a single dopant atom. For the purpose of elucidating the proposed picture, this calculation is performed without anchoring the dopant concentration to the averaged hole density. We find that both the local pair potential (i.e., d -wave OP, see Fig. 1(a)) is enhanced on the sites belonging to the plaquette directly below the dopant atom (for brevity, we will call these sites as “on-dopant” sites). This modulation occurs locally and the “healing length” to recover the bulk value is about the bulk superconducting coherence length $\xi \sim 5a$. Associated with the

local hopping matrix element modulation, the hole density also changes. Directly on the off-diagonal impurity, the hole density is depressed and exhibits the Friedel-like oscillations away from the dopant site. It means the corresponding Bose-Einstein condensed holon field is depressed at the dopant site. In addition, Fig. 1 (c-d) show the corresponding changes in the x - and y - oriented RVB bond OP, which are also recovering a bulk mean field solution at a few lattice spacings.

The LDOS is shown in Fig. 2. The LDOS calculated at the “on-dopant” sites clearly shows an enhanced gap with a V -shaped bottom. Interestingly, it is found that the lost spectral weight at low energy is transferred to the band edge rather than to enhance the height of the coherent peaks at the gap edge. The “on-dopant” gap Δ_1 is larger than the bulk value of the gap Δ_0 . Gap enhancement is about 20% for our choice of parameters. Enhancement clearly depends on the extent to which we increase a local hopping matrix element. However, the present result has been sufficient to convey that the gap modulation as measured by the STM experiment is proportional to the local pair potential modulation due to the change in local hopping integral of electrons. It is qualitatively different from the case of a single site-diagonal unitary impurity, where the impurity-site LDOS does not show the shift of the gap edge though the d -wave OP has been strongly suppressed [9]. The contrast between locally large gap Δ_1 and the sample bulk gap Δ_0 is shown in Fig. 3. For the voltage bias at $E = \Delta_1$, the only bright spot is on the location corresponding to the dopant atom. For the bias at $E = \Delta_0$, the bulk of the sample is bright and the only dark region is on the dopant site.

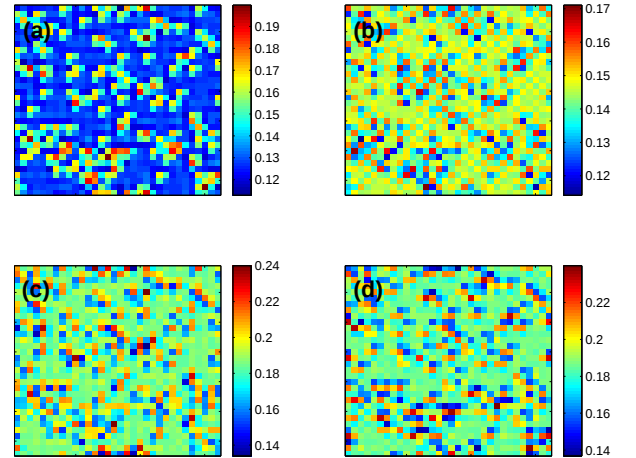


FIG. 4: Same as Fig. 1 but for a concentration of 14% dopants. Here we have assumed that each dopant atom produces one hole. The distribution of dopant atoms is random.

many dopant atoms. To strengthen our proposal of dopant-induced pairing interaction modulation, we turn to the case of multiple dopants, which is more relevant

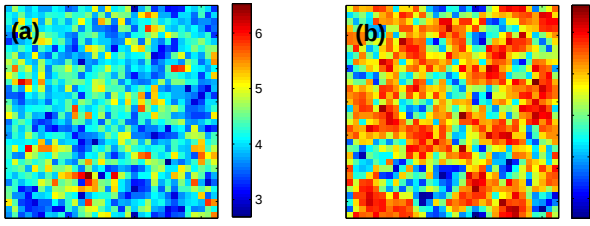


FIG. 5: LDOS $\rho_i(E)$ map at $E = \Delta_1$ (a) and $E = \Delta_0$ (b) for a concentration of 14% dopant atoms.

to the experimental situation. Here we assume that each oxygen dopant contribute one hole to the Cu-O plane. Therefore, we tie the concentration of dopant to the average hole density in the Cu-O plane, i.e., about 14%. As shown Fig. 4, the large pair potential regions are locally registered to the dopant positions, which are randomly distributed. The corresponding hole density map shows the variations that are anti-correlated with the large gap regions. Local x - and y - oriented RVB OP also are registered to the dopant locations. Figure 5 shows the LDOS map at the voltage bias at $E = \Delta_1$ and Δ_0 , respectively. It demonstrates again that the intensity map at $E = \Delta_1$ exhibits a positive correlation with the locally large pair potential regions (the mixed color areas in 4(a)) while that at $E = \Delta_0$ reflects the small pair potential regions (the blue areas in 4(a)).

In conclusion, we have argued that the local gap inhomogeneity can be modeled by the modulation in the local superexchange interaction, induced by the dopant atoms. In the proposed strongly correlated electronic model, the local pairing interaction is controlled by the superexchange interaction. Therefore, in the presence of the interstitial dopant atoms, the strongest effect of the doping would be an off-diagonal disorder that modulates superexchange on the neighboring bonds. Changes in the local superexchange lead to the local changes in the pairing strength and, in turn, in the local magnitude of the d -wave gap. An negative correlation of the hole density variation with the dopant location is also found. The self-consistent calculations also shows that the regions of large gap are registered to the dopant atoms. Large gap regions exhibit smaller and broader coherence peaks. These results are qualitatively consistent with recent STM observations by [6, 23], such as positive correlation between large gap regions and oxygen dopant positions. For a reasonable choice of parameters, we find the gap variations by about 20%. Although we use a specific RVB-like model, we believe the effect of local gap increase to be a general property of any model, where the pairing interaction is set by local superexchange. The following remarks are in order: (i) Our slave-boson mean-field calculation shows an increase of the average gap with a decreased doping, where the dopant concentration becomes more dilute. The result is reasonably consistent with the

experimental data [19]. However, at this moment, we are unable to clarify whether the large gap in the low doping regime is dominated by the proximity to competing orderings; (ii) Although the unscreened electrostatic potentials generated by the oxygen dopants do not tune the local pairing interaction in the proposed model, they might still play a role in the local electronic structure; (iii) To fully address various aspects of nanoscale electronic inhomogeneity in high- T_c cuprates, a minimal effective model should take into account both the site-diagonal and off-diagonal disorder generated by the oxygen dopants, the resultant modulation in the superexchange interaction associated with the off-diagonal disorder, and possibly the residual Hubbard interaction.

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